

Green Products

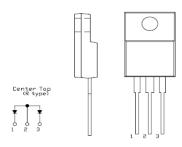
MBRF20150CTR SCHOTTKY RECTIFIER

Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

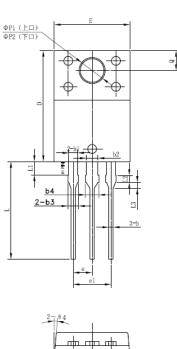
- 175 °C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- . Guard ring for enhanced ruggedness and long term reliability
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

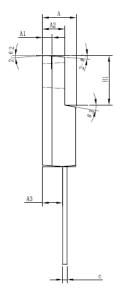


OUTLINE DRAWING

MAX.

Mechanical Dimensions: In mm





Α	4.30	4.50	4.70
A A1	1.10 2.80	1.30	1.50 3.20
A2	2.80	3.00	3.20
A3	2.50	2.70	2.90
A3 b	0.50	0.60	0.75
b1	2.50 0.50 1.10	3.00 2.70 0.60 1.20	2.90 0.75 1.35
b2	1.50	1.60	1.75
b3	1.20	1.30	1.45
b4	1.60	1.70	1.85 0.75
С	0.55	0.60	0.75
b4 c D E	14.80	15.00 10.16	15.20
Е	9.96	10.16	10.36
е		2.55	
e e1 H1 L L1 L2 L3		2.55 5.10 6.70	
H1	6.50	6.70	6.90
L	12.70 1.60	13.20 1.80 1.00 0.80	13.70 2.00 1.20 1.00 3.70
L1	1.60	1.80	2.00
L2	0.80	1.00	1.20
L3	0.60	0.80	1.00
ΦP1(上口)	3.30	3.50	3.70
ΦP2 (下口)	2.99	3.19	3.39
Q	2.50	2.70	2.90
ΦΡ2(下口) Q Θ1 Θ2 Θ3		3.50 3.19 2.70 5° 4° 10° 5° 5°	
Θ2		4°	
Θ3		10°	
Θ4 Θ5		5°	
Θ5		5°	

MIN

TYP.

SYMBOL

2-	0 4	
	- 95	

ITO-220AB(HD)

- China Germany Korea Singapore United States
 - http://www.smc-diodes.com sales@ smc-diodes.com •



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Marking Diagram:



Cautions: Molding resin Epoxy resin UL:94V-0 Where XXXXX is YYWWL

MBR = Device Type F = Package type

20 = Forward Current (20A) 150 = Reverse Voltage (150V)

CTR = Configuration

SSG = SSG YY = Year WW = Week L = Lot Number

Ordering Information:

Device	Package	Shipping
MBRF20150CTR	ITO-220AB	FOrce / tube
	(Pb-Free)	50pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	150	V
Average Forward Current	I _{F(AV)}	50% duty cycle @T _C =100°C, rectangular wave form	10(per leg) 20(per device)	Α
Peak One Cycle Non- Repetitive Surge Current (per leg)	I _{FSM}	8.3 ms, half Sine pulse	150	Α

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Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop	V_{F1}	@ 10A, Pulse, T _J = 25 °C	0.90	V
(per leg) *	V_{F2}	@ 10A, Pulse, T _J = 125 °C	0.80	V
Reverse Current (per leg) *	I _{R1}	$@V_R = \text{rated } V_R$ $T_J = 25 ^{\circ}\text{C}$	1.0	mA
Reverse Current (per leg) *	I _{R2}	$@V_R = \text{rated } V_R$ $T_J = 125 ^{\circ}C$	6.0	mA
Junction Capacitance (per leg)	Ст	$@V_R = 5V, T_C = 25 °C$ $f_{SIG} = 1MHz$	400	pF

^{*} Pulse Width < 300µs, Duty Cycle <2%

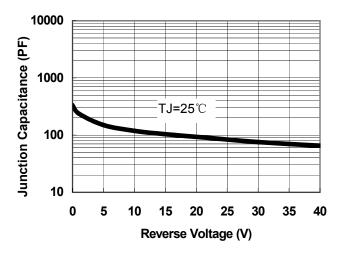
Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Maximum Thermal Resistance Junction to Case (per leg)	$R_{ heta JC}$	DC operation	3.5	°C/W
Approximate Weight	wt	-	2	g
Case Style		ITO-220AB		·

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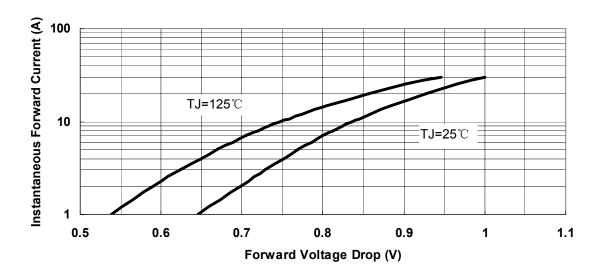
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Instantaneous Reverse Current (µ A) 100 10 TJ=125℃ TJ=25°C 0.1 0.01 30 70 80 100 50 60 Percent of Rated Peak Reverse Voltage (%)

Fig.1-Typical Junction Capacitance

Fig.2-Typical Reverse Characteristics



1000

Fig.3-Typical Instantaneous Forward Voltage Characteristics

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